

### 30V P-Channel Power MOSFET



SOP-8



#### Pin Definition:

Source
Source
Source
Drain
Source
Drain
Gate

#### **Key Parameter Performance**

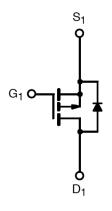
Parameter		Value	Unit	
$V_{ t DS}$		-30	V	
R <sub>DS(on)</sub> (max)	V <sub>GS</sub> = -10V	18		
	V <sub>GS</sub> = -4.5V	30	mΩ	
$Q_g$		14.6	nC	

#### **Ordering Information**

Part No.	Package	Packing		
TSM180P03CS RLG	SOP-8	2.5kpcs / 13" Reel		

**Note:** "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

#### **Block Diagram**



P-Channel MOSFET

### Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	-30	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Ocaliana Paris Ocara I	Tc=25°C	I <sub>D</sub>	-10	Α
Continuous Drain Current	Tc=100°C		-6.3	Α
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	-40	Α
Power Dissipation @ T <sub>C</sub> = 25°C		P <sub>D</sub>	2.5	W
Operating Junction Temperature		TJ	150	°C
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Ambient	R <sub>eJA</sub>	50	°C/W

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Electrical Specifications (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250\mu A$	BV <sub>DSS</sub>	-30			V
Drain-Source On-State Resistance	$V_{GS} = -10V, I_D = -8A$	R <sub>DS(ON)</sub>		14	18	mΩ
	$V_{GS} = -4.5V, I_D = -6A$			23	30	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	V <sub>GS(TH)</sub>	-1.2	-1.6	-2.5	V
7 0	$V_{DS} = -30V, V_{GS} = 0V$				-1	μΑ
Zero Gate Voltage Drain Current	V <sub>DS</sub> = -24V, T <sub>J</sub> = 125°C	I <sub>DSS</sub>			-10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Forward Transconductance (Note 2)	$V_{DS} = -10V, I_{D} = -8A$	<b>g</b> fs		10.5		S
Dynamic				l		
Total Gate Charge (Note 2,3)		$Q_g$		14.6		nC
Gate-Source Charge (Note 2,3)	$V_{DS} = -15V, I_{D} = -8A,$	$Q_{gs}$		4.1		
Gate-Drain Charge (Note 2,3)	$V_{GS} = -4.5V$	$Q_{gd}$		6.3		
Input Capacitance		C <sub>iss</sub>		1730		
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$	Coss		180		pF
Reverse Transfer Capacitance	f = 1.0MHz	$C_{rss}$		125		
Switching				L		
Turn-On Delay Time (Note 2,3)		t <sub>d(on)</sub>		9		
Turn-On Rise Time (Note 2,3)	$V_{DD} = -15V, I_{D} = -1A,$	t <sub>r</sub>		21.8		
Turn-Off Delay Time (Note 2,3)	$V_{GS} = -10V$ , $R_{GEN} = 6\Omega$	t <sub>d(off)</sub>		59.8		ns
Turn-Off Fall Time (Note 2,3)		t <sub>f</sub>		14.4		
Source-Drain Diode Ratings and Ch	aracteristic			L		
Maximum Continuous Drain-Source		ı			40	_
Diode Forward Current	Integral reverse diode in the MOSFET	Is			-10	Α
Maximum Pulse Drain-Source Diode		I <sub>SM</sub>			-40	Α
Forward Current						
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = -1A$	$V_{SD}$			-1	V

#### Note:

- 1. Pulse width limited by safe operating area
- 2. Pulse test: pulse width ≤300µs, duty cycle ≤2%
- 3. Switching time is essentially independent of operating temperature.

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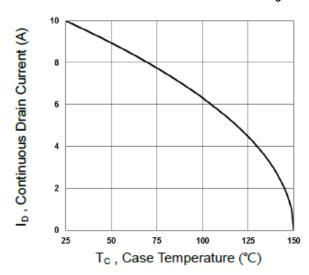


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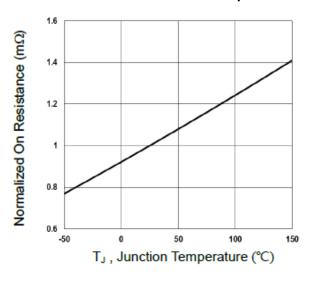
# Pb ROHS COMPLIANT

#### **Electrical Characteristics Curve**

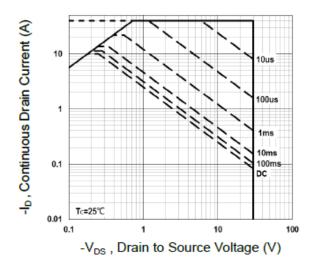
#### Continuous Drain Current vs. Tc



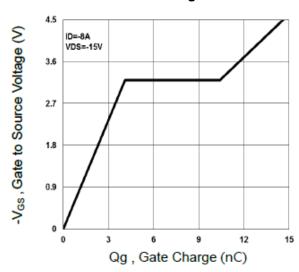
#### On-Resistance vs. Junction Temperature



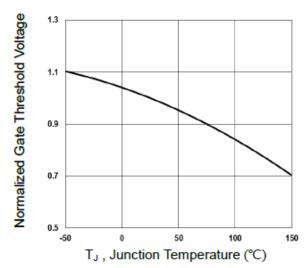
#### **Maximum Safe Operating Area**



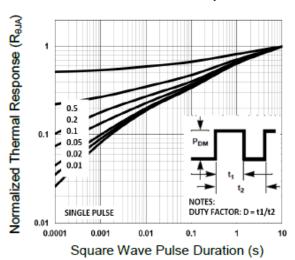
**Gate Charge** 



Threshold Voltage vs. Junction Temperature



#### **Normalized Thermal Transient Impedance Curve**



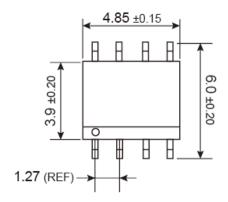
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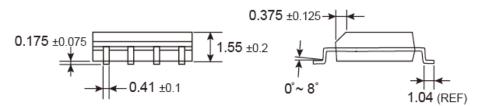


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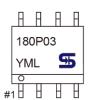
### **SOP-8 Mechanical Drawing**





Unit: Millimeters

### **Marking Diagram**



Y = Year Code

M = Month Code for Halogen Free Product
(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

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L = Lot Code

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### TSM180P03CS 30V P-Channel Power MOSFET

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